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FDP8443_F085 N-Channel PowerTrench[®] MOSFET FAIRCHILD March 2009 SEMICONDUCTOR® FDP8443_F085 N-Channel PowerTrench[®] MOSFET **40V, 80A, 3.5m**Ω **Applications** Features • Typ $r_{DS(on)}$ = 2.7m Ω at V_{GS} = 10V, I_D = 80A Automotive Engine Control ■ Typ Q_{q(10)} = 142nC at V_{GS} = 10V Powertrain Management Solenoid and Motor Drivers ■ Low Miller Charge ■ Low Q_{rr} Body Diode Electronic Steering ■ UIS Capability (Single Pulse and Repetitive Pulse) Integrated Starter / Alternator Qualified to AEC Q101 Distributed Power Architecture and VRMs RoHS Compliant Primary Switch for 12V Systems ROHS D DRAIN SOURCE (FLANGE) DRAIN GATE TO-220AB FDP SERIES

FDP8443_F085 Rev. A

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Symbol	Parameter	Ratings	Units
V _{DSS}	Drain to Source Voltage	40	V
V _{GS}	Gate to Source Voltage	±20	V
	Drain Current Continuous (T _C < 144 ^o C, V _{GS} = 10V)	80	
I _D	Continuous ($T_{amb} = 25^{\circ}C$, $V_{GS} = 10V$, with $R_{\theta JA} = 62^{\circ}C/W$)	20	Α
	Pulsed	See Figure 4	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	531	mJ
П	Power Dissipation	188	W
P _D	Derate above 25°C	1.25	W/ºC
T _J , T _{STG}	Operating and Storage Temperature	-55 to +175	°C

Thermal Characteristics

$R_{ ext{ heta}JC}$	Thermal Resistance Junction to Case		0.8	°C/W
R_{\thetaJA}	Thermal Resistance Junction to Ambient	(Note 2)	62	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP8443	FDP8443_F085	TO-220AB	Tube	N/A	50 units

Electrical Characteristics T_{C} = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units

Off Characteristics

B_{VDSS}	Drain to Source Breakdown Voltage	I _D = 250μA, V _{GS}	s = 0V	40	-	-	V
	Zero Gate Voltage Drain Current	V _{DS} = 32V,		-	-	1	۸
DSS	Zero Gale voltage Drain Current	$V_{GS} = 0V$	T _C = 150°C	-	-	250	μA
I _{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V			-	±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	2	2.8	4	V
		I _D = 80A, V _{GS} = 10V	-	2.7	3.5	
r _{DS(on)}	Drain to Source On Resistance	$I_D = 80A, V_{GS} = 10V,$ $T_J = 175^{\circ}C$	-	4.7	6.1	mΩ

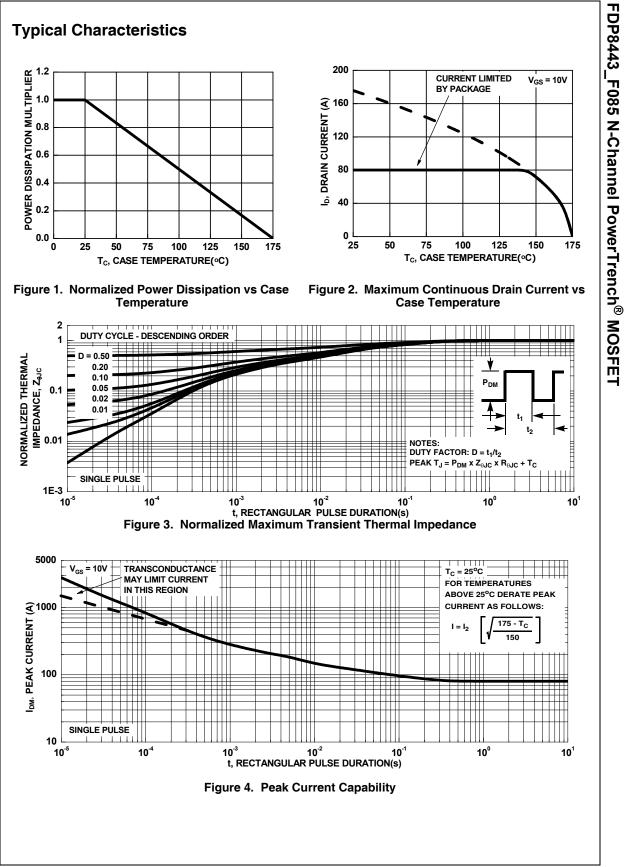
Dynamic Characteristics

C _{iss}	Input Capacitance		0) /	-	9310	-	pF
C _{oss}	Output Capacitance	─ V _{DS} = 25V, V _{GS} = f = 1MHz	$V_{DS} = 25V, V_{GS} = 0V,$		800	-	pF
C _{rss}	Reverse Transfer Capacitance			-	510	-	pF
R _G	Gate Resistance	V _{GS} = 0.5V, f = 1M	lHz	-	0.9	-	Ω
Q _{g(TOT)}	Total Gate Charge at 10V	V _{GS} = 0 to 10V		-	142	185	nC
Q _{g(TH)}	Threshold Gate Charge	V_{GS} = 0 to 2V	V _{DD} = 20V	-	17.5	23	nC
Q _{gs}	Gate to Source Gate Charge		I _D = 35A	-	36	-	nC
Q _{gs2}	Gate Charge Threshold to Plateau		l _g = 1mA	-	18.8	-	nC
Q _{gd}	Gate to Drain "Miller" Charge			-	32	-	nC

Rise Time $V_{DD} = 20V, I_D = 35A$ -17.9-ns $d(off)$ Turn-Off Delay Time $V_{GS} = 10V, R_{GS} = 2\Omega$ -55-ns $fall Time$ -13.5-ns off Turn-Off Time-109nsPrain-Source Diode Characteristics V_{SD} Source to Drain Diode Voltage $I_{SD} = 35A$ -0.81.25V $I_{SD} = 15A$ -0.81.0V	Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Switch	ning Characteristics (V _{GS}	= 10V)				
$\begin{array}{c c c c c c c }\hline & Turn-On Delay Time & & \\ \hline & Rise Time & & \\ \hline & I(off) & Turn-Off Delay Time & & \\ \hline & Gff & Turn-Off Delay Time & & \\ \hline & Fall Time & & \\ \hline & Turn-Off Time & & \\ \hline & Turn-Of$	on	Turn-On Time		-	-	58	ns
Rise Time d(off)VDD = 20V, ID = 35A VGS = 10V, RGS = 20-17.9-nsid(off)Turn-Off Delay Time SoftVGS = 10V, RGS = 20-55-nsid(off)Turn-Off Time-13.5-nsid(off)Turn-Off Time-109nsid(off)Turn-Off Time-109nsifTurn-Off Time-0.81.25-ifSource to Drain Diode VoltageISD = 35A-0.81.0ifV-0.81.0VifReverse Recovery Time ISDISD = 35A, dISD/dt = 100A/µs-4255nsifSource to Drain Diode VoltageISD = 35A, dISD/dt = 100A/µs-4862nC	d(on)	Turn-On Delay Time		-	18.4	-	ns
$\begin{array}{c c c c c c c }\hline & Turn-Off Delay Time \\ \hline & Fall Time \\ \hline & Fall Time \\ \hline & Turn-Off Time \\ \hline \\ \hline \\ rescaled{figure} \\ \hline \\ rspin \\ \hline $	r	Rise Time	$V_{DD} = 20V, I_D = 35A$	-	17.9	-	ns
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	d(off)	Turn-Off Delay Time	$V_{GS} = 100, R_{GS} = 202$	-	55	-	ns
Train-Source Diode CharacteristicsVSDSource to Drain Diode Voltage $I_{SD} = 35A$ -0.81.25VrReverse Recovery Time D_{rr} $I_{SD} = 35A, dI_{SD}/dt = 100A/\mu s$ -4255nsotest:-4862nC	f	Fall Time		-	13.5	-	ns
$ \frac{I_{SD} = 35A}{I_{SD} = 15A} - \frac{0.8}{1.25} V $ $ \frac{I_{SD} = 35A}{I_{SD} = 15A} - \frac{0.8}{1.0} V $ $ \frac{I_{SD} = 15A}{I_{SD} = 35A, dI_{SD}/dt} = 100A/\mu s $ $ \frac{I_{SD} = 35A, dI_{SD}/dt}{I_{SD} = 35A, dI_{SD}/dt} = 100A/\mu s $	off	Turn-Off Time		-	-	109	ns
Source to Drain Diode Voltage $OD = 15A$ - 0.8 1.0 VrReverse Recovery Time $I_{SD} = 35A$, $dI_{SD}/dt = 100A/\mu s$ - 42 55 ns Q_{rr} Reverse Recovery Charge $I_{SD} = 35A$, $dI_{SD}/dt = 100A/\mu s$ - 48 62 nCotes:	rain-S	ource Diode Characteristics					
Source to Drain Diode Voltage $OD = 15A$ - 0.8 1.0 VrReverse Recovery Time $I_{SD} = 35A$, $dI_{SD}/dt = 100A/\mu s$ - 42 55 ns Q_{rr} Reverse Recovery Charge $I_{SD} = 35A$, $dI_{SD}/dt = 100A/\mu s$ - 48 62 nCotes:			I _{SD} = 35A	-	0.8	1.25	
rReverse Recovery TimeI_{SD} = 35A, dI_{SD}/dt = 100A/\mus-4255ns ρ_{rr} Reverse Recovery ChargeI_{SD} = 35A, dI_{SD}/dt = 100A/\mus-4862nContes:	SD	Source to Drain Diode Voltage		-			V
P_{rr} Reverse Recovery Charge $I_{SD} = 35A, dI_{SD}/dt = 100A/\mu s$ - 48 62 nC	rr	Reverse Recovery Time		-			ns
otes:		Reverse Recovery Charge	$I_{SD} = 35A$, $dI_{SD}/dt = 100A/\mu s$	-	48	62	nC
	Pulse widt	J = 25 [°] C, L = 0.26mH, I _{AS} = 64A. h = 100s.					

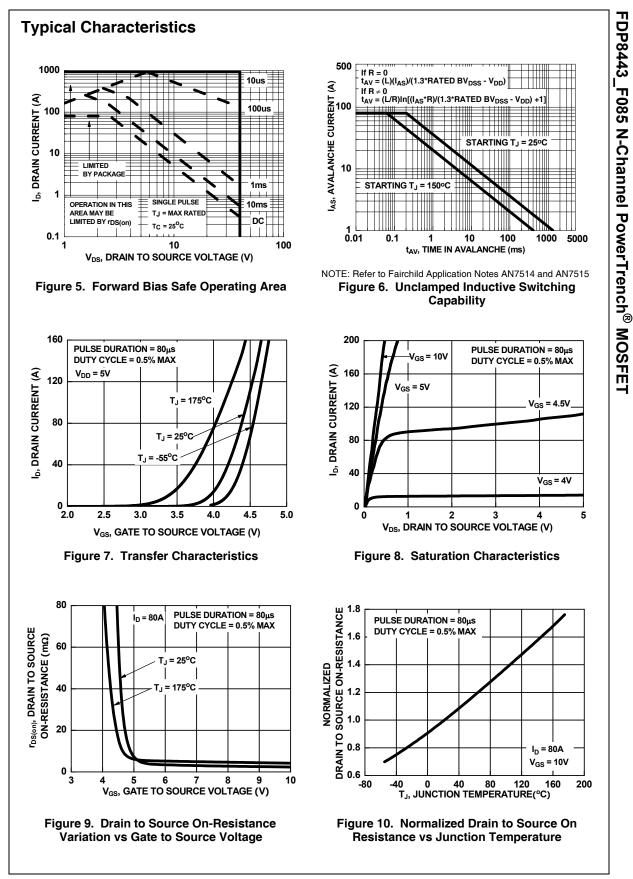
designed to meet the extreme test conditions and environment demanded by the automotive industry. For

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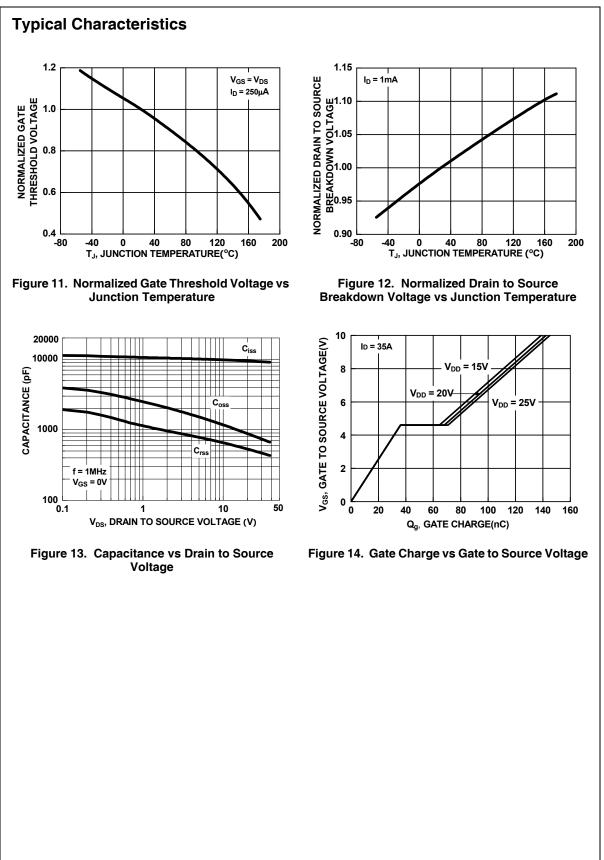


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